

Alois Lugstein

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152
papers

2,921
citations

28
h-index

47
g-index

159
ext. papers

3,256
ext. citations

5.6
avg, IF

4.89
L-index

#	Paper	IF	Citations
152	Integrating an ultramicroelectrode in an AFM cantilever: combined technology for enhanced information. <i>Analytical Chemistry</i> , 2001 , 73, 2491-500	7.8	267
151	Deep-ultraviolet solar-blind photoconductivity of individual gallium oxide nanobelts. <i>Nanoscale</i> , 2011 , 3, 1120-6	7.7	172
150	Integrated AFM-SECM in tapping mode: simultaneous topographical and electrochemical imaging of enzyme activity. <i>Angewandte Chemie - International Edition</i> , 2003 , 42, 3238-40	16.4	135
149	Tuning the electro-optical properties of germanium nanowires by tensile strain. <i>Nano Letters</i> , 2012 , 12, 6230-4	11.5	104
148	Anomalous piezoresistance effect in ultrastrained silicon nanowires. <i>Nano Letters</i> , 2010 , 10, 3204-8	11.5	92
147	Pressure-induced orientation control of the growth of epitaxial silicon nanowires. <i>Nano Letters</i> , 2008 , 8, 2310-4	11.5	86
146	Combined scanning electrochemical atomic force microscopy for tapping mode imaging. <i>Applied Physics Letters</i> , 2003 , 82, 1592-1594	3.4	67
145	FIB processing of silicon in the nanoscale regime. <i>Applied Physics A: Materials Science and Processing</i> , 2003 , 76, 545-548	2.6	62
144	Atomic scale alignment of copper-germanide contacts for ge nanowire metal oxide field effect transistors. <i>Nano Letters</i> , 2009 , 9, 3739-42	11.5	57
143	Integrating micro- and nanoelectrodes into atomic force microscopy cantilevers using focused ion beam techniques. <i>Applied Physics Letters</i> , 2002 , 81, 349-351	3.4	55
142	Full three-dimensional simulation of focused ion beam micro/nanofabrication. <i>Nanotechnology</i> , 2007 , 18, 245303	3.4	52
141	Current density profile extraction of focused ion beams based on atomic force microscopy contour profiling of nanodots. <i>Journal of Applied Physics</i> , 2002 , 92, 4037-4042	2.5	51
140	Numerical simulation of scanning electrochemical microscopy experiments with frame-shaped integrated atomic force microscopy-SECM probes using the boundary element method. <i>Analytical Chemistry</i> , 2005 , 77, 764-71	7.8	50
139	Hydroisomerization and cracking of n-octane and C8 isomers on Ni-containing zeolites. <i>Applied Catalysis A: General</i> , 1999 , 176, 119-128	5.1	50
138	Simulation of ion beam induced micro/nano fabrication. <i>Journal of Micromechanics and Microengineering</i> , 2007 , 17, 1178-1183	2	42
137	Simulation of ion beam direct structuring for 3D nanoimprint template fabrication. <i>Microelectronic Engineering</i> , 2006 , 83, 936-939	2.5	42
136	Ultrafast VLS growth of epitaxial beta- Ga(2)O(3) nanowires. <i>Nanotechnology</i> , 2009 , 20, 434017	3.4	39

135	Fabrication of a ring nanoelectrode in an AFM tip: novel approach towards simultaneous electrochemical and topographical imaging. <i>Surface and Interface Analysis</i> , 2002 , 33, 146-150	1.5	39
134	Abrupt Schottky Junctions in Al/Ge Nanowire Heterostructures. <i>Nano Letters</i> , 2015 , 15, 4783-7	11.5	38
133	Dynamics of hydrogen adsorption on promoter-and inhibitor-modified nickel surfaces. <i>Chemical Physics</i> , 1993 , 177, 421-431	2.3	36
132	Microwave-Assisted Ge _{1-x} Sn _x Nanowire Synthesis: Precursor Species and Growth Regimes. <i>Chemistry of Materials</i> , 2015 , 27, 6125-6130	9.6	34
131	In operando x-ray imaging of nanoscale devices: Composition, valence, and internal electrical fields. <i>Science Advances</i> , 2017 , 3, eaao4044	14.3	33
130	Orientation specific synthesis of kinked silicon nanowires grown by the vapour-liquid-solid mechanism. <i>Nanotechnology</i> , 2009 , 20, 125606	3.4	31
129	Hydroconversion of n-heptane over bifunctional HZSM5 zeolites influence of the metal concentration and distribution on the activity and selectivity. <i>Applied Catalysis A: General</i> , 1998 , 166, 29-38	5.1	31
128	Focused ion beam induced surface amorphization and sputter processes. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003 , 21, 927		31
127	Comparison of impregnation, liquid- and solid-state ion exchange procedures for the incorporation of nickel in HMFI, HMOR and HBEA. <i>Microporous and Mesoporous Materials</i> , 2000 , 39, 307-317	5.3	31
126	Origin of anomalous piezoresistive effects in VLS grown Si nanowires. <i>Nano Letters</i> , 2015 , 15, 1780-5	11.5	30
125	In Situ Transmission Electron Microscopy Analysis of Aluminum-Germanium Nanowire Solid-State Reaction. <i>Nano Letters</i> , 2019 , 19, 2897-2904	11.5	29
124	Direct Synthesis of Hyperdoped Germanium Nanowires. <i>ACS Nano</i> , 2018 , 12, 1236-1241	16.7	26
123	Fabrication of cone-shaped boron doped diamond and gold nanoelectrodes for AFM-SECM. <i>Nanotechnology</i> , 2011 , 22, 145306	3.4	26
122	Growth of branched single-crystalline GaAs whiskers on Si nanowire trunks. <i>Nanotechnology</i> , 2007 , 18, 355306	3.4	26
121	Electrochemical current-sensing atomic force microscopy in conductive solutions. <i>Nanotechnology</i> , 2013 , 24, 115501	3.4	25
120	Quantitative scanning capacitance spectroscopy. <i>Applied Physics Letters</i> , 2003 , 83, 4253-4255	3.4	25
119	Room-Temperature Quantum Ballistic Transport in Monolithic Ultrascaled Al-Ge-Al Nanowire Heterostructures. <i>Nano Letters</i> , 2017 , 17, 4556-4561	11.5	24
118	Some aspects of substrate pretreatment for epitaxial Si nanowire growth. <i>Nanotechnology</i> , 2008 , 19, 485606	3.4	24

117	Self-aligned coupled cavity GaAs/AlGaAs midinfrared quantum-cascade laser. <i>Applied Physics Letters</i> , 2000 , 77, 1077-1079	3.4	24
116	Electrical transport properties of single-crystal Al nanowires. <i>Nanotechnology</i> , 2016 , 27, 385704	3.4	23
115	Epitaxial GeSn Nanowires for Nanoscale Mid-Infrared Emitters. <i>ACS Nano</i> , 2019 , 13, 8047-8054	16.7	23
114	GaAu alloy catalyst for single crystal silicon-nanowire epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 023109	3.4	23
113	Atomic force microscopy-scanning electrochemical microscopy: influence of tip geometry and insulation defects on diffusion controlled currents at conical electrodes. <i>Analytical Chemistry</i> , 2011 , 83, 2971-7	7.8	21
112	Scalable approach for vertical device integration of epitaxial nanowires. <i>Nano Letters</i> , 2009 , 9, 1830-4	11.5	21
111	Co-containing zeolites prepared by solid-state ion exchange. <i>Journal of the Chemical Society, Faraday Transactions</i> , 1997 , 93, 4091-4094		21
110	Level set approach for the simulation of focused ion beam processing on the micro/nano scale. <i>Nanotechnology</i> , 2007 , 18, 265307	3.4	21
109	Study of focused ion beam response of GaAs in the nanoscale regime. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 2238		21
108	Multimode silicon nanowire transistors. <i>Nano Letters</i> , 2014 , 14, 6699-703	11.5	20
107	Size and site controlled Ga nanodots on GaAs seeded by focused ion beams. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 888		20
106	Anomalous Plastic Deformation and Sputtering of Ion Irradiated Silicon Nanowires. <i>Nano Letters</i> , 2015 , 15, 3800-7	11.5	19
105	Ultrascaled Germanium Nanowires for Highly Sensitive Photodetection at the Quantum Ballistic Limit. <i>Nano Letters</i> , 2018 , 18, 5030-5035	11.5	19
104	Dynamical Tuning of Nanowire Lasing Spectra. <i>Nano Letters</i> , 2017 , 17, 6637-6643	11.5	18
103	Simulation-based approach for the accurate fabrication of blazed grating structures by FIB. <i>Optics Express</i> , 2007 , 15, 9444-9	3.3	18
102	Slow trap response of zirconium dioxide thin films on silicon. <i>Applied Physics Letters</i> , 2003 , 83, 1400-1402	3.4	18
101	Quantum cascade lasers with monolithic air-semiconductor Bragg reflectors. <i>Applied Physics Letters</i> , 2000 , 77, 1241-1243	3.4	18
100	Subeutectic synthesis of epitaxial Si-NWs with diverse catalysts using a novel Si precursor. <i>Nano Letters</i> , 2010 , 10, 3957-61	11.5	17

99	Characterization of metallic species on Ni- and Co-containing ZSM-5 catalysts. Reduction behavior and catalytic properties. <i>Zeolites</i> , 1997 , 18, 391-397		17
98	Tuning the electrical performance of Ge nanowire MOSFETs by focused ion beam implantation. <i>Nanotechnology</i> , 2011 , 22, 035201	3.4	16
97	Hydroconversion of n-heptane over CoNi containing HZSM5. <i>Applied Catalysis A: General</i> , 1997 , 152, 93-105	10.5	15
96	Electrical characterization and examination of temperature-induced degradation of metastable GeSn nanowires. <i>Nanoscale</i> , 2018 , 10, 19443-19449	7.7	15
95	Atypical self-activation of Ga dopant for Ge nanowire devices. <i>Nano Letters</i> , 2011 , 11, 3108-12	11.5	14
94	Low power phase change memory switching of ultra-thin In ₃ Sb ₁ Te ₂ nanowires. <i>Applied Physics Letters</i> , 2016 , 109, 213103	3.4	14
93	Strain distribution in single, suspended germanium nanowires studied using nanofocused x-rays. <i>Nanotechnology</i> , 2016 , 27, 055705	3.4	13
92	Scanning electrochemical microscopy: Diffusion controlled approach curves for conical AFM-SECM tips. <i>Electrochemistry Communications</i> , 2013 , 27, 29-33	5.1	13
91	High performance gated Ge nanowire MOSFET with quasi-metallic source/drain contacts. <i>Nanotechnology</i> , 2010 , 21, 435704	3.4	13
90	Measuring the Optical Absorption of Single Nanowires. <i>Physical Review Applied</i> , 2020 , 14,	4.3	13
89	Solution-based low-temperature synthesis of germanium nanorods and nanowires. <i>Monatshefte für Chemie</i> , 2018 , 149, 1315-1320	1.4	12
88	III-V semiconductor nanocrystal formation in silicon nanowires via liquid-phase epitaxy. <i>Nano Research</i> , 2014 , 7, 1769-1776	10	12
87	Focused electron beam induced deposition of gold catalyst templates for Si-nanowire synthesis. <i>Nanotechnology</i> , 2011 , 22, 015302	3.4	12
86	Synthesis of nanowires in room temperature ambient: A focused ion beam approach. <i>Applied Physics Letters</i> , 2006 , 88, 163114	3.4	12
85	Scanning capacitance microscopy investigations of focused ion beam damage in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 19, 178-182	3	12
84	Method to characterize the three-dimensional distribution of focused ion beam induced damage in silicon after 50 keV Ga ⁺ irradiation. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2003 , 21, 1644-1648	2.9	12
83	Monolithic Axial and Radial Metal-Semiconductor Nanowire Heterostructures. <i>Nano Letters</i> , 2018 , 18, 7692-7697	11.5	12
82	In situ monitoring of Joule heating effects in germanium nanowires by Raman spectroscopy. <i>Nanotechnology</i> , 2013 , 24, 065701	3.4	11

81	Study of focused ion beam response of GaSb. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 255, 309-313	1.2	11
80	A novel fabrication technique for crystallite growth on a (1 0 0) InAs surface utilizing focused ion beams. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 222, 91-95	1.2	11
79	AFM-Tip-Integrated Amperometric Microbiosensors: High-Resolution Imaging of Membrane Transport. <i>Angewandte Chemie</i> , 2005 , 117, 3485-3488	3.6	11
78	Synthesis, Morphological, and Electro-optical Characterizations of Metal/Semiconductor Nanowire Heterostructures. <i>Nano Letters</i> , 2016 , 16, 3507-13	11.5	11
77	Electric field modulation of thermovoltage in single-layer MoS ₂ . <i>Applied Physics Letters</i> , 2014 , 105, 253103	3.4	10
76	Ultra-fast vapour-liquid-solid synthesis of Si nanowires using ion-beam implanted gallium as catalyst. <i>Nanotechnology</i> , 2011 , 22, 395601	3.4	10
75	n-Heptane cracking on H- and Ni-containing zeolites. <i>Journal of the Chemical Society, Faraday Transactions</i> , 1997 , 93, 1837-1842		10
74	Silicene Passivation by Few-Layer Graphene. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 12745-12754	3.4	9
73	Plasmon-Driven Hot Electron Transfer at Atomically Sharp Metal-Semiconductor Nanojunctions. <i>ACS Photonics</i> , 2020 , 7, 1642-1648	6.3	9
72	Focused ion beam generated antimony nanowires for microscale pH sensors. <i>Applied Physics Letters</i> , 2009 , 95, 223106	3.4	9
71	Nanoscale aluminum plasmonic waveguide with monolithically integrated germanium detector. <i>Applied Physics Letters</i> , 2019 , 115, 161107	3.4	8
70	CMOS-Compatible Controlled Hyperdoping of Silicon Nanowires. <i>Advanced Materials Interfaces</i> , 2018 , 5, 1800101	4.6	8
69	Electrostatic actuated strain engineering in monolithically integrated VLS grown silicon nanowires. <i>Nanotechnology</i> , 2014 , 25, 455705	3.4	8
68	Focused ion beam induced nanodot and nanofiber growth. <i>Microelectronic Engineering</i> , 2006 , 83, 1491-1494	3.4	8
67	Focussed ion beam induced damage in silicon studied by scanning capacitance microscopy. <i>Semiconductor Science and Technology</i> , 2003 , 18, 195-198	1.8	8
66	Highly Transparent Contacts to the 1D Hole Gas in Ultrascaled Ge/Si Core/Shell Nanowires. <i>ACS Nano</i> , 2019 , 13, 14145-14151	16.7	8
65	The high pressure phase transformation behavior of silicon nanowires. <i>Applied Physics Letters</i> , 2018 , 113, 123103	3.4	8
64	Gate-Tunable Negative Differential Resistance in Next-Generation Ge Nanodevices and their Performance Metrics. <i>Advanced Electronic Materials</i> , 2021 , 7, 2001178	6.4	8

63	Gate-Tunable Electron Transport Phenomena in Al-Ge<111>-Al Nanowire Heterostructures. <i>Nano Letters</i> , 2015 , 15, 7514-8	11.5	7
62	Nanowires enabling strained photovoltaics. <i>Applied Physics Letters</i> , 2014 , 104, 163901	3.4	7
61	Impact of fluence-rate related effects on the sputtering of silicon at elevated target temperatures. <i>Journal of Applied Physics</i> , 2009 , 105, 044912	2.5	7
60	In situ micro-Raman compression: characterization of plasticity and fracture in GaAs. <i>Philosophical Magazine</i> , 2011 , 91, 1286-1292	1.6	7
59	Focused ion beam induced synthesis of a porous antimony nanowire network. <i>Journal of Applied Physics</i> , 2007 , 102, 044308	2.5	7
58	Polarity Control in Ge Nanowires by Electronic Surface Doping. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 19858-19863	3.8	7
57	Combined Optical and Electronic Readout for Event Reconstruction in a GEM-Based TPC. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 913-918	1.7	6
56	Nano-patterning and growth of self-assembled quantum dots. <i>Microelectronics Journal</i> , 2006 , 37, 1532-1584		6
55	Nanometer-Scale Ge-Based Adaptable Transistors Providing Programmable Negative Differential Resistance Enabling Multivalued Logic. <i>ACS Nano</i> , 2021 ,	16.7	6
54	Tuning Electroluminescence from a Plasmonic Cavity-Coupled Silicon Light Source. <i>Nano Letters</i> , 2018 , 18, 7230-7237	11.5	6
53	Drastic Changes in Material Composition and Electrical Properties of Gallium-Seeded Germanium Nanowires. <i>Crystal Growth and Design</i> , 2019 , 19, 2531-2536	3.5	5
52	Strain engineering of core-shell silicon carbide nanowires for mechanical and piezoresistive characterizations. <i>Nanotechnology</i> , 2019 , 30, 265702	3.4	5
51	In Situ Transmission Electron Microscopy Analysis of Copper-Germanium Nanowire Solid-State Reaction. <i>Nano Letters</i> , 2019 , 19, 8365-8371	11.5	5
50	Impact of growth temperature on the crystal habits, forms and structures of VO ₂ nanocrystals. <i>Applied Physics A: Materials Science and Processing</i> , 2011 , 102, 201-204	2.6	5
49	Growth of one-dimensional III-V structures on Si nanowires and pre-treated planar Si surfaces. <i>Journal of Crystal Growth</i> , 2009 , 311, 1859-1862	1.6	5
48	Spatially resolved thermoelectric effects in semiconductor-metal nanowire heterostructures. <i>Nanoscale</i> , 2020 , 12, 20590-20597	7.7	5
47	In-doped Sb nanowires grown by MOCVD for high speed phase change memories. <i>Micro and Nano Engineering</i> , 2019 , 2, 117-121	3.4	5
46	Quasi One-Dimensional Metal-Semiconductor Heterostructures. <i>Nano Letters</i> , 2019 , 19, 3892-3897	11.5	4

45	In-Situ Transmission Electron Microscopy Imaging of Aluminum Diffusion in Germanium Nanowires for the Fabrication of Sub-10 nm Ge Quantum Disks. <i>ACS Applied Nano Materials</i> , 2020 , 3, 1891-1899	5.6	4
44	Coulomb blockade in monolithic and monocrystalline Al-Ge-Al nanowire heterostructures. <i>Applied Physics Letters</i> , 2020 , 116, 013105	3.4	4
43	A general approach toward shape-controlled synthesis of silicon nanowires. <i>Nano Letters</i> , 2013 , 13, 21-511.5	11.5	4
42	Synthesis and electrical characterization of intrinsic and in situ doped Si nanowires using a novel precursor. <i>Beilstein Journal of Nanotechnology</i> , 2012 , 3, 564-9	3	4
41	Sputter-redeposition method for the fabrication of automatically sealed micro/nanochannel using FIBs. <i>International Journal of Precision Engineering and Manufacturing</i> , 2011 , 12, 893-898	1.7	4
40	Superconducting MgB2 weak links and superconducting quantum interference devices prepared by AFM nanolithography. <i>Physica C: Superconductivity and Its Applications</i> , 2008 , 468, 789-792	1.3	4
39	Study of the chemical and morphological evolution of the GaAs surface after high fluence focused ion beam exposure. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 217, 402-408	1.2	4
38	Monolithic Metal-Semiconductor-Metal Heterostructures Enabling Next-Generation Germanium Nanodevices. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 12393-12399	9.5	4
37	Reversible Al Propagation in Si Ge Nanowires: Implications for Electrical Contact Formation. <i>ACS Applied Nano Materials</i> , 2020 , 3, 10427-10436	5.6	3
36	Focused ion beam induced synthesis of antimony nanowires for gas sensor applications. <i>Nanotechnology</i> , 2012 , 23, 435502	3.4	3
35	Anisotropic lithiation behavior of crystalline silicon. <i>Nanotechnology</i> , 2012 , 23, 495716	3.4	3
34	Nano-bridges based on the superconducting MgB2 thin films. <i>Physica C: Superconductivity and Its Applications</i> , 2008 , 468, 785-788	1.3	3
33	A Top-Down Platform Enabling Ge Based Reconfigurable Transistors. <i>Advanced Materials Technologies</i> , 2100647	6.8	3
32	Highly Biaxially Strained Silicene on Au(111). <i>Journal of Physical Chemistry C</i> , 2021 , 125, 9973-9980	3.8	3
31	Optical Signatures of Dirac Electrodynamics for hBN-Passivated Silicene on Au(111). <i>Nano Letters</i> , 2021 , 21, 5301-5307	11.5	3
30	Synthesis of Novel Phases in Si Nanowires Using Diamond Anvil Cells at High Pressures and Temperatures. <i>Nano Letters</i> , 2021 , 21, 1427-1433	11.5	3
29	Miniaturized Wide-Range Field-Emission Vacuum Gauge. <i>Nanomaterials and Nanotechnology</i> , 2014 , 4, 29	2.9	2
28	RTS and 1/f noise in Ge nanowire transistors 2011 ,		2

27	Nanowire-metal heterostructures for high performance MOSFETs. <i>Elektrotechnik Und Informationstechnik</i> , 2010 , 127, 171-175	0.4	2
26	FIB induced growth of antimony nanowires. <i>Microelectronic Engineering</i> , 2007 , 84, 1440-1442	2.5	2
25	Bias-Switchable Photoconductance in a Nanoscale Ge Photodetector Operated in the Negative Differential Resistance Regime. <i>ACS Photonics</i> ,	6.3	2
24	Ge quantum wire memristor. <i>Nanotechnology</i> , 2020 , 31, 445204	3.4	2
23	Polycrystalline Ge Nanosheets Embedded in Metal-Semiconductor Heterostructures Enabling Wafer-Scale 3D Integration of Ge Nanodevices with Self-Aligned Al Contacts. <i>Advanced Electronic Materials</i> , 2021 , 7, 2100101	6.4	2
22	Formation of n- and p-type regions in individual Si/SiO core/shell nanowires by ion beam doping. <i>Nanotechnology</i> , 2018 , 29, 474001	3.4	2
21	Electromagnetic enhancement effect on the atomically abrupt heterojunction of Si/InAs heterostructured nanowires. <i>Journal of Applied Physics</i> , 2019 , 125, 064303	2.5	1
20	Stimulated Raman Scattering in Ge Nanowires. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 13872-13877	3.8	1
19	Fabrication and characterization of a germanium nanowire light emitting diode. <i>Applied Physics Letters</i> , 2017 , 111, 233103	3.4	1
18	High temperature focused ion beam response of graphite resulting in spontaneous nanosheet formation. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 061804	1.3	1
17	Local, direct-write, damage-free thinning of germanium nanowires. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 06FB03	1.3	1
16	Impact of Al, Ni, and TiN Metal Gates On ZrO ₂ -MOS Capacitors. <i>ECS Transactions</i> , 2006 , 1, 507-515	1	1
15	Room temperature lasing of electrically pumped quantum cascade micro-cylinders. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 17, 626-628	3	1
14	Ion Beam Induced Chemical Vapor Deposition of Dielectric Materials. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 624, 163		1
13	Transition metal cations in zeolites [A] catalyst for hds reactions. <i>Studies in Surface Science and Catalysis</i> , 1995 , 98, 163-164	1.8	1
12	Electroluminescence from NiSi ₂ /Si/NiSi ₂ nanowire heterostructures operated at high electric fields. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2895-2900	1.6	1
11	Verifying the band gap narrowing in tensile strained Ge nanowires by electrical means. <i>Nanotechnology</i> , 2021 , 32, 145711	3.4	1
10	Al-Ge-Al Nanowire Heterostructure: From Single-Hole Quantum Dot to Josephson Effect. <i>Advanced Materials</i> , 2021 , 33, e2101989	24	1

- 9 Effects of Ga-Irradiation On Properties of Materials Processed by a Focused Ion Beam (FIB). *Materials Research Society Symposia Proceedings*, **2000**, 647, 1 o
- 8 Ytterbium silicide nanostructures prepared by pulsed laser ablation in oven: Structural and electrical characterization. *Materials Letters*, **2019**, 246, 17-19 3.3
- 7 In-situ propagation of Al in germanium nanowires observed by transmission electron microscopy **2016**, 205-206
- 6 Peculiarities of temperature dependent ion beam sputtering and channeling of crystalline bismuth. *Nanotechnology*, **2014**, 25, 305302 3.4
- 5 Metallic nano dots realized by a subtractive self organization process. *Superlattices and Microstructures*, **2004**, 36, 107-111 2.8
- 4 Nonuniform-channel MOS device. *Applied Physics A: Materials Science and Processing*, **2003**, 76, 1035-1039.6
- 3 FIB-TEM Characterization of Locally Restricted Implantation Damage. *Materials Research Society Symposia Proceedings*, **2002**, 738, 7141
- 2 Extended Defects in Semiconductor Nanowires **2008**, 149-150
- 1 In-situ propagation of a Cu phase in germanium nanowires observed by transmission electron microscopy **2016**, 642-643